



74VCXH162245

LOW VOLTAGE CMOS 16-BIT BUS TRANSCEIVER (3-STATE) WITH 3.6V TOLERANT INPUTS AND OUTPUTS

- 3.6V TOLERANT INPUTS AND OUTPUTS
- HIGH SPEED A OUTPUTS:
 $t_{PD} = 3.4 \text{ ns (MAX.)}$ at $V_{CC} = 3.0$ to 3.6V
 $t_{PD} = 4.3 \text{ ns (MAX.)}$ at $V_{CC} = 2.3$ to 2.7V
- SYMMETRICAL IMPEDANCE A OUTPUTS:
 $|I_{OH}| = I_{OL} = 12 \text{ mA (MIN)}$ at $V_{CC} = 3.0\text{V}$
 $|I_{OH}| = I_{OL} = 8 \text{ mA (MIN)}$ at $V_{CC} = 2.3\text{V}$
- HIGH SPEED B OUTPUTS:
 $t_{PD} = 2.5 \text{ ns (MAX.)}$ at $V_{CC} = 3.0$ to 3.6V
 $t_{PD} = 3.2 \text{ ns (MAX.)}$ at $V_{CC} = 2.3$ to 2.7V
- SYMMETRICAL IMPEDANCE B OUTPUTS:
 $|I_{OH}| = I_{OL} = 24 \text{ mA (MIN)}$ at $V_{CC} = 3.0\text{V}$
 $|I_{OH}| = I_{OL} = 18 \text{ mA (MIN)}$ at $V_{CC} = 2.3\text{V}$
- POWER-DOWN PROTECTION ON INPUTS AND OUTPUTS
- 26Ω SERIES RESISTORS IN A PORT OUTPUT
- OPERATING VOLTAGE RANGE:
 $V_{CC} \text{ (OPR)} = 2.3\text{V}$ to 3.6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 16245
- BUS HOLD PROVIDED ON BOTH SIDES
- LATCH-UP PERFORMANCE EXCEEDS 300mA
- ESD PERFORMANCE:
 $\text{HBM} > 2000\text{V}$; $\text{MM} > 200\text{V}$

DESCRIPTION

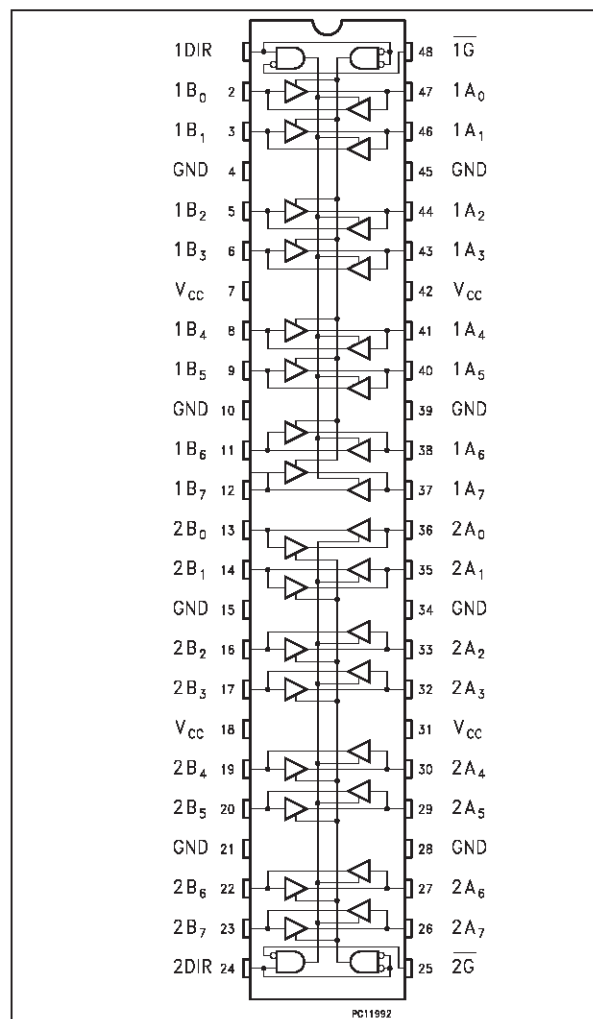
The VCXH162245 is a low voltage CMOS 16-BIT BUS TRANSCEIVER (3-STATE) fabricated with sub-micron silicon gate and five layer metal wiring C²MOS technology. It is ideal for low power and very high speed 2.3 to 3.6V applications; it can be interfaced to 3.6V signal environment for both inputs and outputs. This IC is intended for two-way asynchronous communication between data buses; the direction of data transmission is determined by DIR input. The two enable inputs \overline{nG} can be used to disable the device so that the buses are effectively isolated. The device circuit is including 26Ω series resistance in the A port outputs. These resistors permit to reduce line noise in high speed applications. Bus hold on data inputs is provided in order to eliminate the need for external pull-up or pull-down resistor. All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.



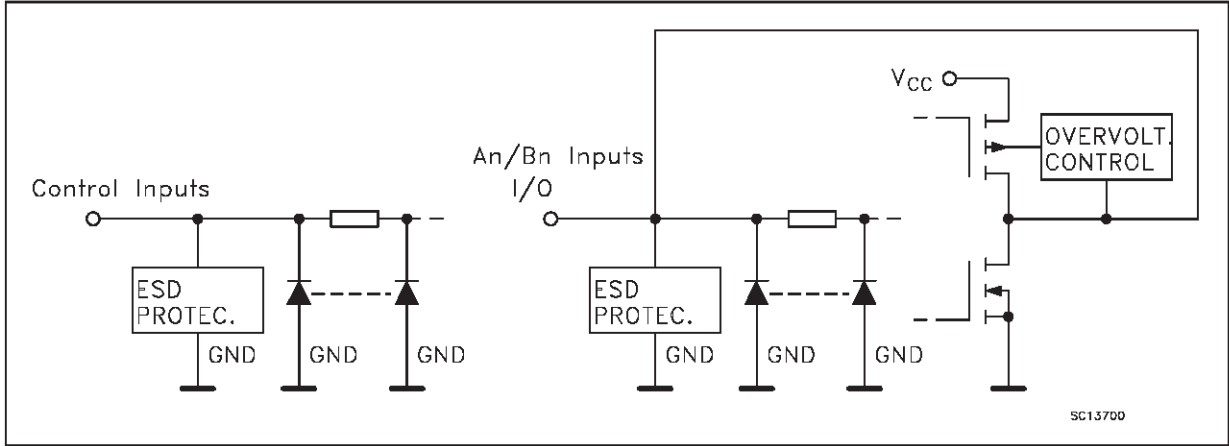
T
(TSSOP48 Package)

ORDER CODES :
74VCXH162245T

PIN CONNECTION



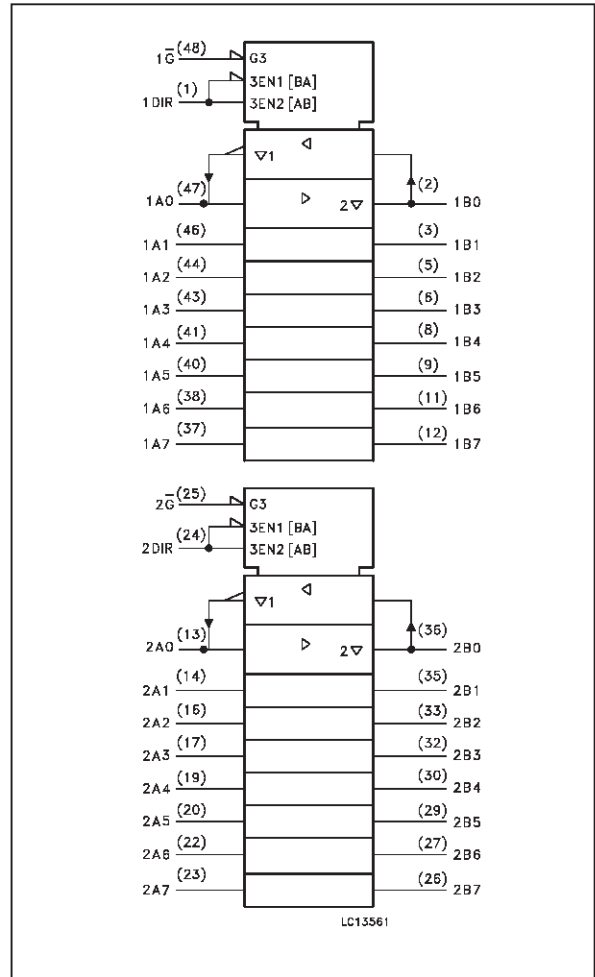
INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1	1DIR	Directional Control
2, 3, 5, 6, 8, 9, 11, 12	1B0 to 1B7	Data Inputs/Outputs
13, 14, 16, 17, 19, 20, 22, 23	2B0 to 2B7	Data Inputs/Outputs
24	2DIR	Directional Control
25	$\overline{2G}$	Output Enable Input
36, 35, 33, 32, 30, 29, 27, 26	2A0 to 2A7	Data Inputs/Outputs
47, 46, 44, 43, 41, 40, 38, 37	1A0 to 1A7	Data Inputs/Outputs
48	$\overline{1G}$	Output Enable Input
4, 10, 15, 21, 28, 34, 39, 45	GND	Ground (0V)
7, 18, 31, 42	V _{CC}	Positive Supply Voltage

IEC LOGIC SYMBOLS



TRUTH TABLE

INPUT		FUNCTION		OUTPUT
\overline{G}	DIR	A BUS	B BUS	
L	L	OUTPUT	INPUT	A = B
L	H	INPUT	OUTPUT	B = A
H	X	Z	Z	Z

X: "H" or "L"
Z: High impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to + 4.6	V
V _I	DC Input Voltage	-0.5 to + 4.6	V
V _O	DC Output Voltage (OFF state)	-0.5 to + 4.6	V
V _O	DC Output Voltage (High or Low State) (note1)	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	- 50	mA
I _{OK}	DC Output Diode Current (note2)	± 50	mA
I _O	DC Output Source/Sink Current	± 50	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current Per Supply Pin	± 100	mA
P _D	Power Dissipation	400	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

1) I_O absolute maximum rating must be observed

2) V_O < GND, V_O > V_{CC}

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2.3 to 3.6	V
V _I	Input Voltage	-0.3 to 3.6	V
V _O	Output Voltage (OFF state)	0 to 3.6	V
V _O	Output Voltage (High or Low State)	0 to V _{CC}	V
I _{OH} , I _{OL}	High or Low Level Output Current - A side (V _{CC} =3.0 to 3.6V)	± 12	mA
I _{OH} , I _{OL}	High or Low Level Output Current - A side (V _{CC} =2.3 to 2.7V)	± 8	mA
I _{OH} , I _{OL}	High or Low Level Output Current - B side (V _{CC} =3.0 to 3.6V)	± 24	mA
I _{OH} , I _{OL}	High or Low Level Output Current - B side (V _{CC} =2.3 to 2.7V)	± 18	mA
T _{op}	Operating Temperature:	-40 to +85	°C
dt/dv	Input Transition Rise or Fall Rate (V _{CC} = 3.0V) (note 1)	0 to 10	ns/V

1) V_{IN} from 0.8V to 2.0V, V_{CC}=3.0V

DC SPECIFICATIONS (2.7V < V_{CC} ≤ 3.6V unless otherwise specified)

Symbol	Parameter	Test Conditions		Value		Unit	
		V _{CC} (V)		-40 to 85 °C			
				Min.	Max.		
V _{IH}	High Level Input Voltage	2.7 to 3.6		2.0		V	
V _{IL}	Low Level Input Voltage				0.8		V
V _{OH}	High Level Output Voltage (A Outputs)	2.7 to 3.6	V _I = V _{IH} or V _{IL}	I _O = -100 μA	V _{CC} - 0.2	V	
		2.7		I _O = -6 mA	2.2		
		3.0		I _O = -8 mA	2.4		
		3.0		I _O = -12 mA	2.2		
V _{OH}	High Level Output Voltage (B Outputs)	2.7 to 3.6	V _I = V _{IH} or V _{IL}	I _O = -100 μA	V _{CC} - 0.2	V	
		2.7		I _O = -12 mA	2.2		
		3.0		I _O = -18 mA	2.4		
		3.0		I _O = -24 mA	2.2		
V _{OL}	Low Level Output Voltage (A Outputs)	2.7 to 3.6	V _I = V _{IH} or V _{IL}	I _O = 100 μA		0.2	
		2.7		I _O = 6 mA		0.4	
		3.0		I _O = 8 mA		0.55	
		3.0		I _O = 12 mA		0.8	
V _{OL}	Low Level Output Voltage (B Outputs)	2.7 to 3.6	V _I = V _{IH} or V _{IL}	I _O = 100 μA		0.2	
		2.7		I _O = 12 mA		0.4	
		3.0		I _O = 18 mA		0.4	
		3.0		I _O = 24 mA		0.55	
I _I	Input Leakage Current	2.7 to 3.6	V _I = V _{CC} or GND			±5	μA
I _{I(HOLD)}	Input Hold Current	3	V _I = 0.8 V	75		μA	
			V _I = 2 V	-75			
		3.6	V _I = 0 to 3.6 V		±500		
I _{OZ}	3 State Output Leakage Current	2.7 to 3.6	V _I = V _{IH} or V _{IL} V _O = 0 to 3.6 V			±10	μA
I _{off}	Power Off Leakage Current	0	V _I or V _O = 0 to 3.6 V			10	μA
I _{CC}	Quiescent Supply Current	2.7 to 3.6	V _I = V _{CC} or GND		20	μA	
			V _I or V _O = V _{CC} to 3.6 V		±20		
ΔI _{CC}	ICC incr. per input	2.7 to 3.6	V _{IH} = V _{CC} - 0.6 V		750	μA	

DC SPECIFICATIONS ($2.3V < V_{CC} \leq 2.7V$ unless otherwise specified)

Symbol	Parameter	Test Conditions		Value		Unit
		V _{CC} (V)		-40 to 85 °C		
				Min.	Max.	
V _{IH}	High Level Input Voltage	2.3 to 2.7			1.6	V
V _{IL}	Low Level Input Voltage				0.7	V
V _{OH}	High Level Output Voltage (A Outputs)	2.3 to 2.7	V _I = V _{IH} or V _{IL}	I _O = -100 μA	V _{CC} - 0.2	V
		2.3		I _O = -4 mA	2.0	
		2.3		I _O = -6 mA	1.8	
		2.3		I _O = -8 mA	1.7	
V _{OH}	High Level Output Voltage (B Outputs)	2.3 to 2.7	V _I = V _{IH} or V _{IL}	I _O = -100 μA	V _{CC} - 0.2	V
		2.3		I _O = -6 mA	2.0	
		2.3		I _O = -12 mA	1.8	
		2.3		I _O = -18 mA	1.7	
V _{OL}	Low Level Output Voltage (A Outputs)	2.3 to 2.7	V _I = V _{IH} or V _{IL}	I _O = 100 μA	0.2	V
		2.3		I _O = 6 mA	0.4	
		2.3		I _O = 8 mA	0.6	
V _{OL}	Low Level Output Voltage (B Outputs)	2.3 to 2.7	V _I = V _{IH} or V _{IL}	I _O = 100 μA	0.2	V
		2.3		I _O = 12 mA	0.4	
		2.3		I _O = 18 mA	0.6	
I _I	Input Leakage Current	2.3 to 2.7	V _I = V _{CC} or GND		±5	μA
I _{I(HOLD)}	Input Hold Current	2.3	V _I = 0.7 V	45		μA
			V _I = 1.7 V	-45		
I _{OZ}	3 State Output Leakage Current	2.3 to 2.7	V _I = V _{IH} or V _{IL} V _O = 0 to 3.6 V		±10	μA
I _{off}	Power Off Leakage Current	0	V _I or V _O = 0 to 3.6 V		10	μA
I _{CC}	Quiescent Supply Current	2.3 to 2.7	V _I = V _{CC} or GND		20	μA
			V _I or V _O = V _{CC} to 3.6 V		±20	

DYNAMIC SWITCHING CHARACTERISTICS ($T_a = 25^\circ\text{C}$, Input $t_r = t_f = 2.0\text{ns}$, $C_L = 30\text{pF}$)

Symbol	Parameter	Test Conditions		Value			Unit
		V _{CC} (V)		T _A = 25 °C			
				Min.	Typ.	Max.	
V _{OLP}	Dynamic Peak Low Voltage Quiet Output (note 1, 3), A to B	2.5	V _{IL} = 0 V V _{IH} = V _{CC}		0.6		V
		3.3			0.8		
V _{OLP}	Dynamic Peak Low Voltage Quiet Output (note 1, 3) B to A	2.5	V _{IL} = 0 V V _{IH} = V _{CC}		0.25		V
		3.3			0.35		
V _{OLV}	Dynamic Valley Low Voltage Quiet Output (note 1, 3) A to B	2.5	V _{IL} = 0 V V _{IH} = V _{CC}		-0.6		V
		3.3			-0.8		
V _{OLV}	Dynamic Valley Low Voltage Quiet Output (note 1, 3) B to A	2.5	V _{IL} = 0 V V _{IH} = V _{CC}		-0.25		V
		3.3			-0.35		
V _{OHV}	Dynamic Valley High Voltage Quiet Output (note 2, 3) A to B	2.5	V _{IL} = 0 V V _{IH} = V _{CC}		1.9		V
		3.3			2.2		
V _{OHV}	Dynamic Valley High Voltage Quiet Output (note 2, 3) B to A	2.5	V _{IL} = 0 V V _{IH} = V _{CC}		2.05		V
		3.3			2.65		

1) Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH to LOW or LOW to HIGH. The remaining output is measured in the LOW state.

2) Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH to LOW or LOW to HIGH. The remaining output is measured in the HIGH state.

3) Parameters guaranteed by design.

AC ELECTRICAL CHARACTERISTICS ($C_L = 30 \text{ pF}$, $R_L = 500 \Omega$, Input $t_r = t_f = 2.0 \text{ ns}$)

Symbol	Parameter	Test Condition		Value		Unit
		V _{CC} (V)	Waveform	-40 to 85 °C		
				Min.	Max.	
t _{PLH} t _{PHL}	Propagation Delay Time A to B	2.3 to 2.7	1	1.0	3.2	ns
		3.0 to 3.6		0.8	2.5	
t _{PLH} t _{PHL}	Propagation Delay Time B to A	2.3 to 2.7	1	1.0	4.3	ns
		3.0 to 3.6		0.8	3.4	
t _{PZL} t _{PZH}	Output Enable Time A to B	2.3 to 2.7	2	1.0	4.9	ns
		3.0 to 3.6		0.8	3.8	
t _{PZL} t _{PZH}	Output Enable Time B to A	2.3 to 2.7	2	1.0	5.7	ns
		3.0 to 3.6		0.8	4.2	
t _{PLZ} t _{PHZ}	Output Disable Time A to B	2.3 to 2.7	2	1.0	4.2	ns
		3.0 to 3.6		0.8	3.7	
t _{PLZ} t _{PHZ}	Output Disable Time B to A	2.3 to 2.7	2	1.0	4.8	ns
		3.0 to 3.6		0.8	4.1	
t _{OSLH} t _{OSHL}	Output to Output Skew Time (note 1, 2)	2.3 to 2.7			0.5	ns
		3.0 to 3.6			0.5	

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW ($t_{OSLH} = |t_{PLHm} - t_{PLHl}|$, $t_{OSHL} = |t_{PHLm} - t_{PHLl}|$)

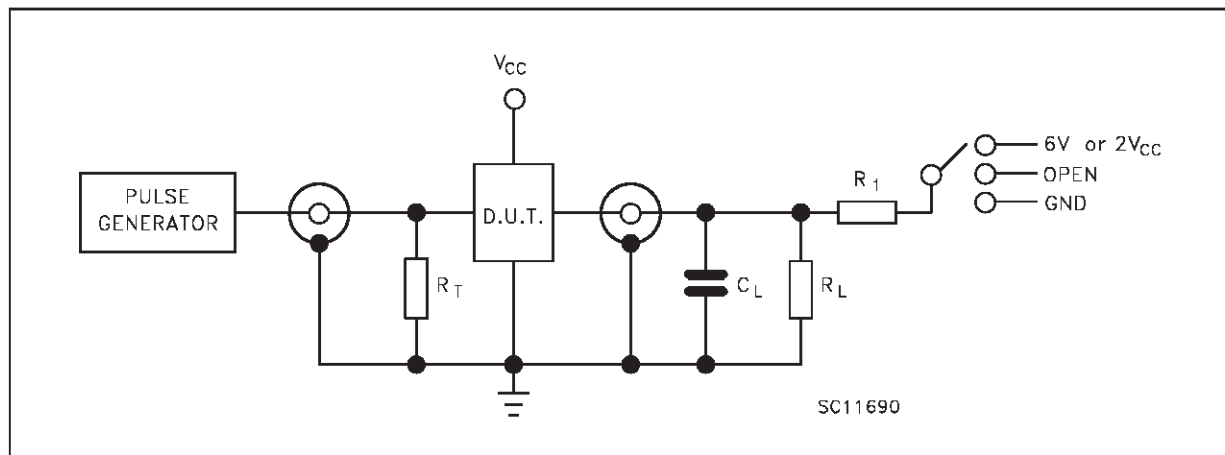
2) Parameter guaranteed by design

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions		Value			Unit
		V _{CC} (V)		T _A = 25 °C			
				Min.	Typ.	Max.	
C _{IN}	Input Capacitance	2.5 or 3.3	V _{IN} = 0V or V _{CC}		4		pF
C _{OUT}	Output Capacitance	2.5 or 3.3	V _{IN} = 0V or V _{CC}		8		pF
C _{PD}	Power Dissipation Capacitance (note 1)	2.5 or 3.3	f _{IN} = 10MHz V _{IN} = 0V or V _{CC}		28		pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/16$ (per circuit)

TEST CIRCUIT



TEST	SWITCH
t_{PLH} , t_{PHL}	Open
t_{PZL} , t_{PLZ} ($V_{CC} = 3.0$ to $3.6V$)	6V
t_{PZL} , t_{PLZ} ($V_{CC} = 2.3$ to $2.7V$)	$2V_{CC}$
t_{PZH} , t_{PHZ}	GND

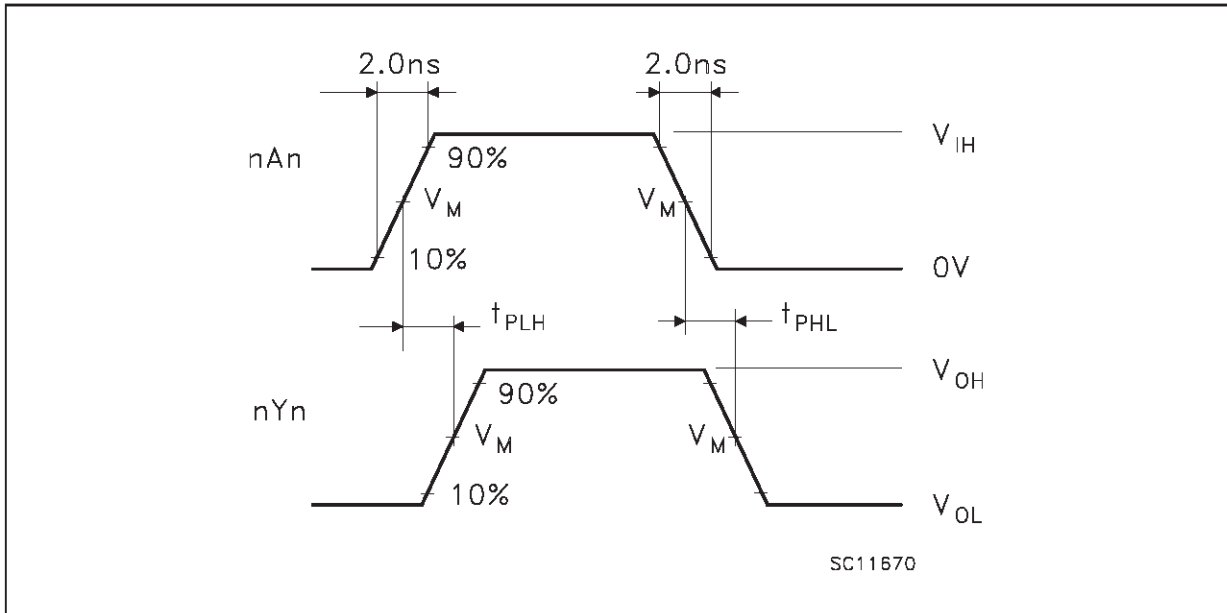
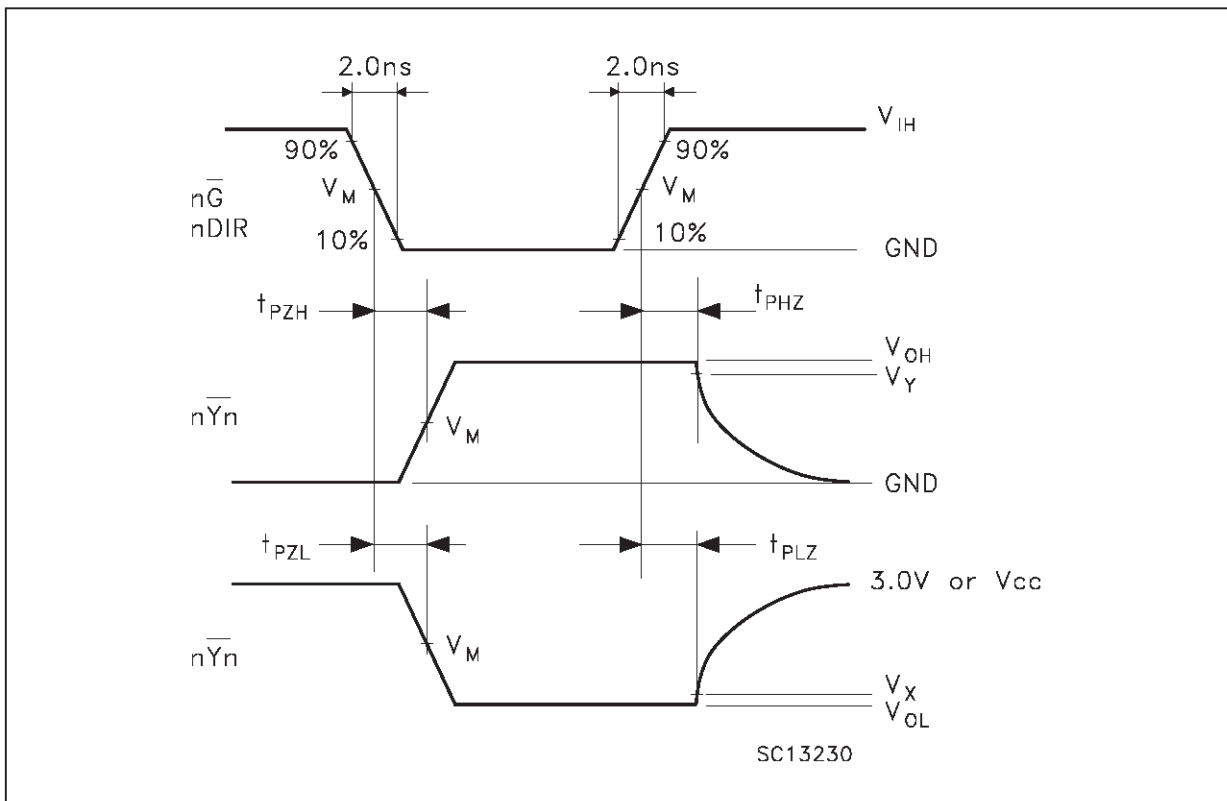
$C_L = 30$ pF or equivalent (includes jig and probe capacitance)

$R_L = R_1 = 500\Omega$ or equivalent

$R_T = Z_{out}$ of pulse generator (typically 50Ω)

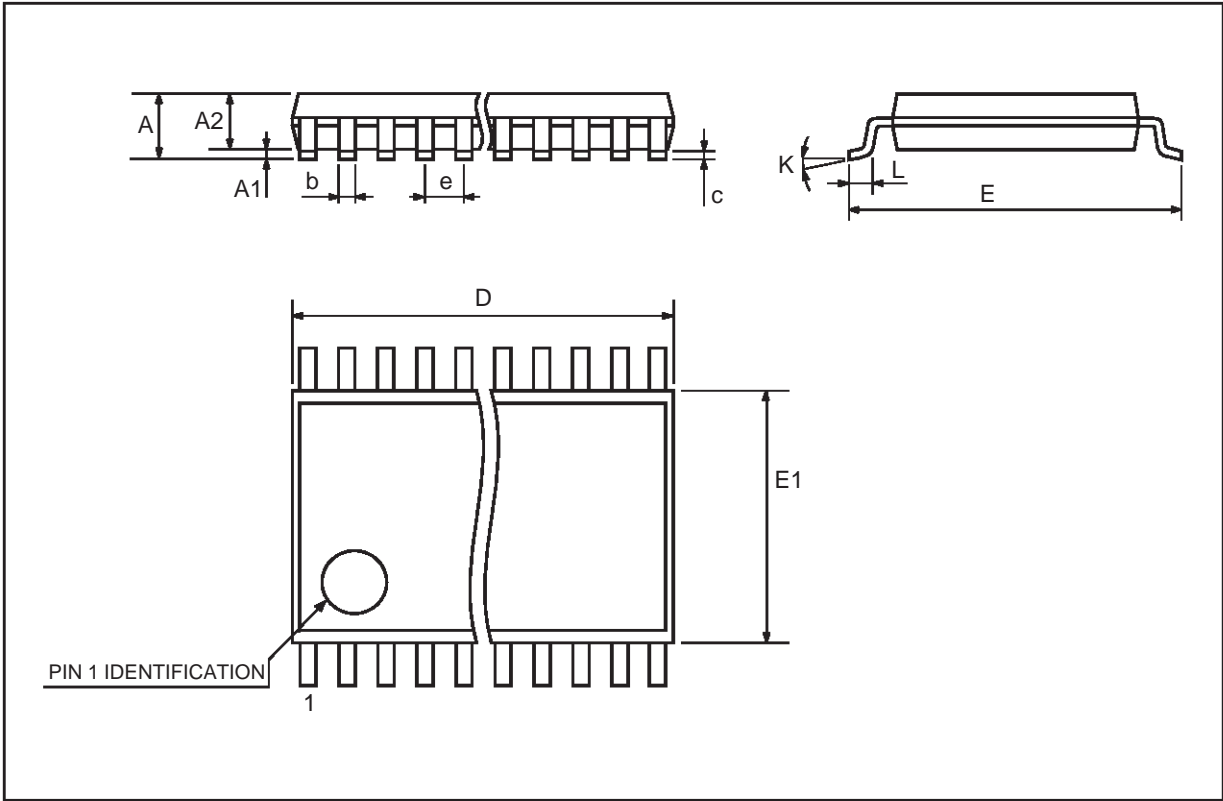
WAVEFORM SYMBOL VALUES

Symbol	V_{CC}	
	3.0 to 3.6V	2.3 to 2.7V
V_{IH}	2.7V	V_{CC}
V_M	1.5V	$V_{CC}/2$
V_X	$V_{OL} + 0.3V$	$V_{OL} + 0.15V$
V_Y	$V_{OH} - 0.3V$	$V_{OH} - 0.15V$

WAVEFORM 1: PROPAGATION DELAYS (f=1MHz; 50% duty cycle)**WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIME** (f=1MHz; 50% duty cycle)

TSSOP48 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.1			0.433
A1	0.05	0.10	0.15	0.002	0.004	0.006
A2	0.85	0.9	0.95	0.335	0.354	0.374
b	0.17		0.27	0.0067		0.011
c	0.09		0.20	0.0035		0.0079
D	12.4	12.5	12.6	0.408	0.492	0.496
E	7.95	8.1	8.25	0.313	0.319	0.325
E1	6.0	6.1	6.2	0.236	0.240	0.244
e		0.5 BSC			0.0197 BSC	
K	0°	4°	8°	0°	4°	8°
L	0.50	0.60	0.70	0.020	0.024	0.028



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